DDTA (R2-ONLY SERIES) E

PNP PRE-BIASED SMALL SIGNAL SOT-523 SURFACE MOUNT TRANSISTOR

NEW PRODUCT

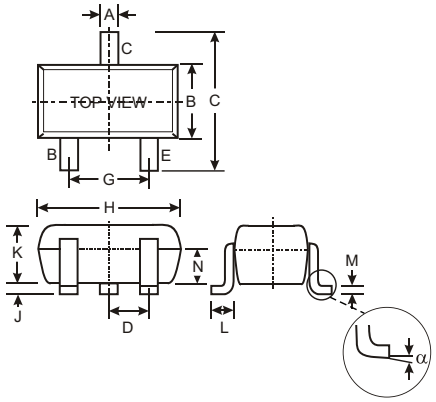
Features

- Epitaxial Planar Die Construction
- Complementary NPN Types Available (DDTC)
- Built-In Biasing Resistor, R2 only
- Also Available in Lead Free Version

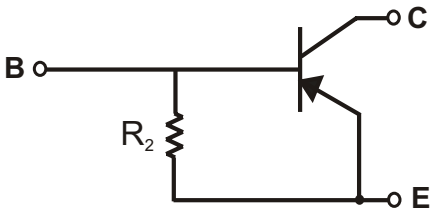
Mechanical Data

- Case: SOT-523, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish). Please see Ordering Information, Note 3, on Page 2
- Terminal Connections: See Diagram
- Marking: Date Code and Marking Code (See Diagrams & Page 2)
- Weight: 0.002 grams (approx.)
- Ordering Information (See Page 2)

P/N	R2 (NOM)	MARKING
DDTA114GE	10KΩ	P26
DDTA124GE	22KΩ	P27
DDTA144GE	47KΩ	P28
DDTA115GE	100KΩ	P29



SOT-523			
Dim	Min	Max	Typ
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50
α	0°	8°	—
All Dimensions in mm			



SCHEMATIC DIAGRAM

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C (Max)	-100	mA
Power Dissipation	P_d	150	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{\theta JA}$	833	°C/W
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	°C

Note: 1. Mounted on FR4 PC Board with recommended pad layout at http://www.diodes.com/datasheets/ap02001.pdf.

NEW PRODUCT

Electrical Characteristics @ $T_A = 25°C$ unless otherwise specified

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV_{CBO}	-50	—	—	V	I_C = -50μA
Collector-Emitter Breakdown Voltage		BV_{CEO}	-50	—	—	V	I_C = -1mA
Emitter-Base Breakdown Voltage		BV_{EBO}	5	—	—	V	I_E = -720μA, DDTA114GE I_E = -330μA, DDTA124GE I_E = -160μA, DDTA144GE I_E = -72μA, DDTA115GE
Collector Cutoff Current		I_{CBO}	—	—	-0.5	μA	V_{CB} = -50V
Emitter Cutoff Current	DDTA114GE DDTA124GE DDTA144GE DDTA115GE	I_{EBO}	-300 -140 -65 -30	—	-580 -260 -130 -58	μA	V_{EB} = -4V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	—	—	-0.3	V	I_C = -10mA, I_B = -0.5mA
DC Current Transfer Ratio	DDTA114GE DDTA124GE DDTA144GE DDTA115GE	h_{FE}	30 56 68 82	—	—	—	I_C = -5mA, V_{CE} = -5V
Bleeder Resistor (R_2) Tolerance		DR_2	-30	—	+30	%	—
Gain-Bandwidth Product*		f_T	—	250	—	MHz	V_{CE} = -10V, I_E = 5mA, f = 100MHz

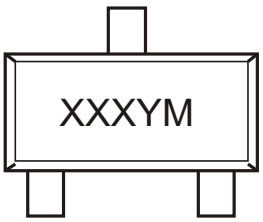
* Transistor - For Reference Only

Ordering Information (Note 2)

Device	Packaging	Shipping
DDTA114GE-7	SOT-523	3000/Tape & Reel
DDTA124GE-7	SOT-523	3000/Tape & Reel
DDTA144GE-7	SOT-523	3000/Tape & Reel
DDTA115GE-7	SOT-523	3000/Tape & Reel

Notes: 2. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.
3. For Lead Free version (with Lead Free terminal finish) part number, please add "-F" suffix to part number above. Example: DDTA115GE-7-F.

Marking Information



XXX = Product Type Marking Code (See Page 1, e.g. P26 = DDTA114GE)
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009
Code	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

TYPICAL CURVES - DDTA114GE

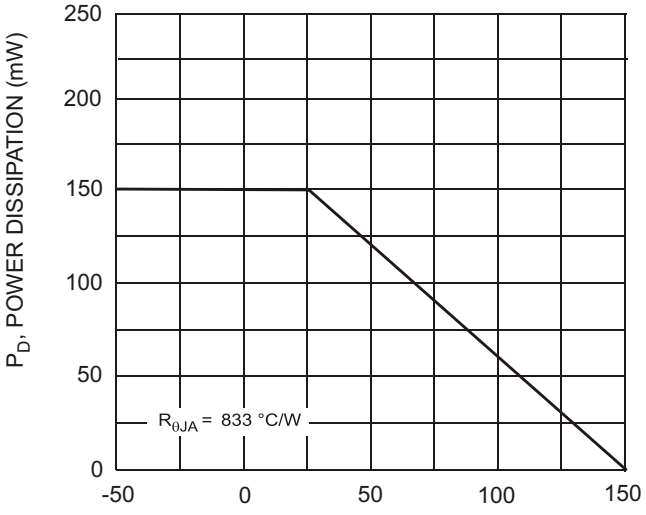


Fig. 1, Derating Curve

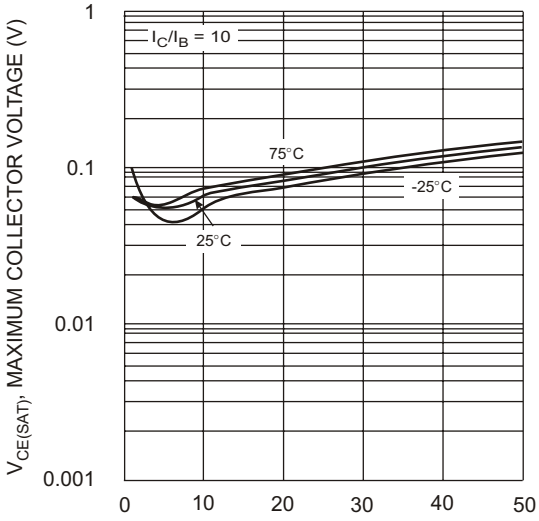


Fig. 2 $V_{CE(SAT)}$ vs. I_C

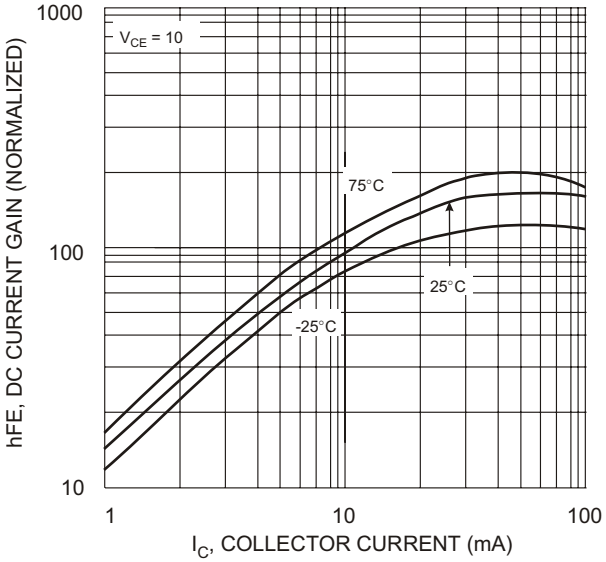


Fig. 3 DC Current Gain

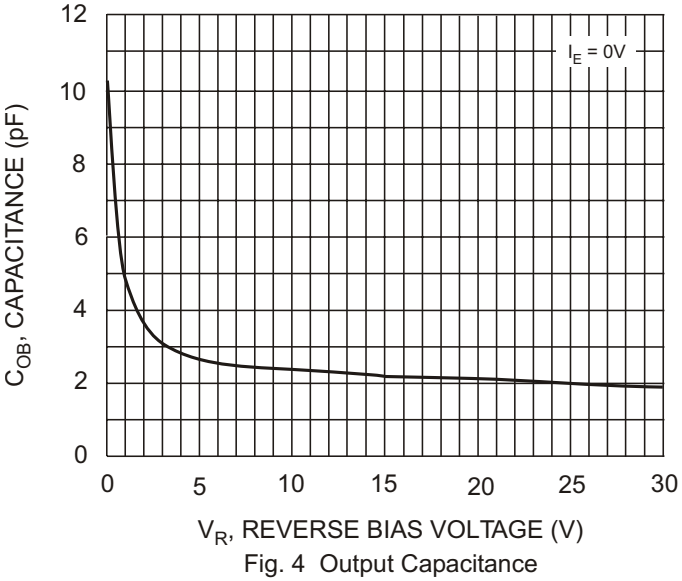


Fig. 4 Output Capacitance

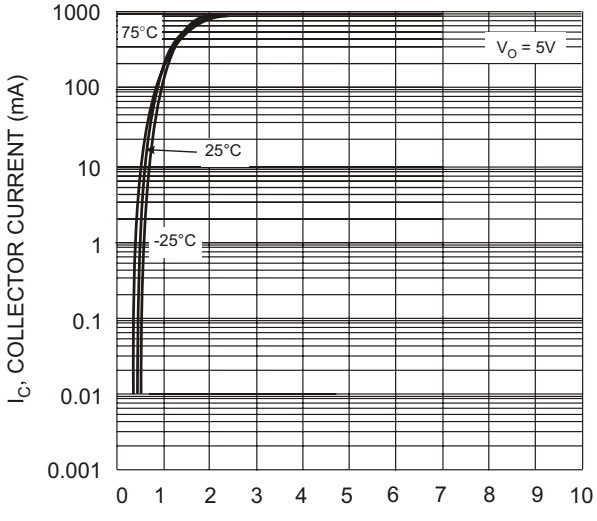


Fig. 5 Collector Current Vs. Input Voltage

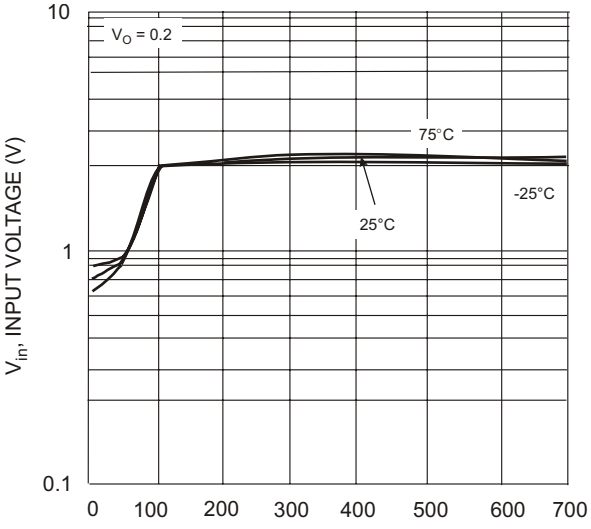


Fig. 6 Input Voltage vs. Collector Current

littlediode
COMPONENTS FOR ALL

Littlediode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.